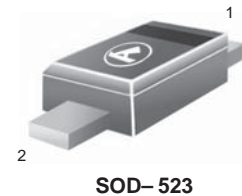


Variable Capacitance Diode for VCO

HVC362



FEATURES

- High capacitance ratio. (n =3.0.min)
- Good C-V linearity.
- Ultra small Flat Package (UFP) is suitable for surface mount design.



DEVICE MARKING

HVC362 = V2

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C)

| Item | Symbol | Value | Unit |
|----------------------|------------------|--------------|------|
| Reverse voltage | V _R | 15 | V |
| Junction temperature | T _j | 125 | °C |
| Storage temperature | T _{stg} | - 55 to +125 | °C |

Notes 1. R_L = 10kΩ

ELECTRICAL CHARACTERISTICS (T_A = 25°C)

| Item | Symbol | Min | Typ | Max | Unit | Test Condition |
|-------------------|-----------------|------|-----|------|------|--|
| Reverse current | I _{R1} | - | - | 10 | nA | V _R = 10V |
| | I _{R2} | - | - | 100 | | V _R = 10V, T _A = 60°C |
| Capacitance | C ₁ | 41.6 | - | 49.9 | pF | V _R = 1V, f = 1 MHz |
| | C ₄ | 10.1 | - | 14.8 | | V _R = 4V, f = 1 MHz |
| Capacitance ratio | n | 3.0 | - | - | - | C ₁ / C ₄ |
| Series resistance | r _s | - | - | 2.0 | Ω | V _R = 4V, f = 100 MHz |
| ESD-Capability*1 | - | 80 | - | - | V | *C = 200pF, Both forward and reverse direction 1 pulse. |

Notes 1. Failure criterion ; I_R ≥ 20nA at V_R = 10 V

HVC362

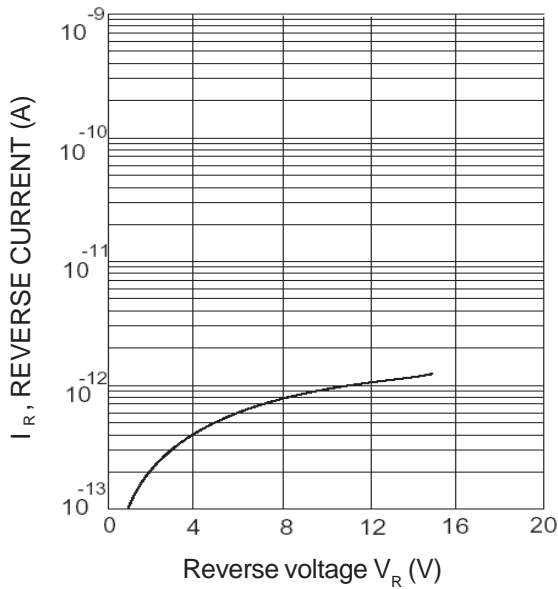


Fig.1 Reverse current Vs. Reverse voltage

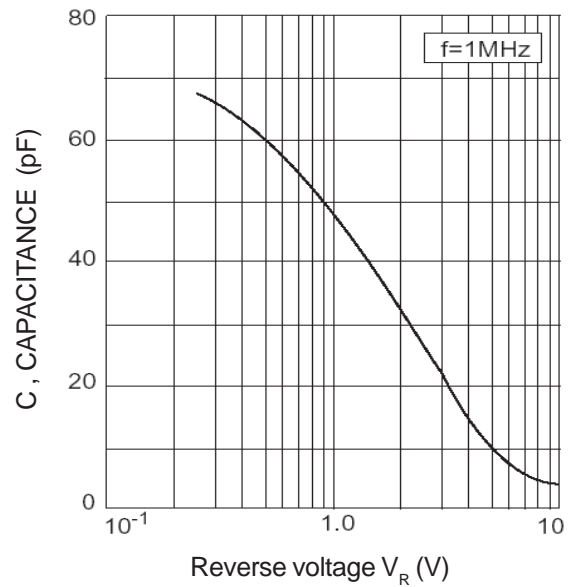


Fig.2 Capacitance Vs. Reverse voltage

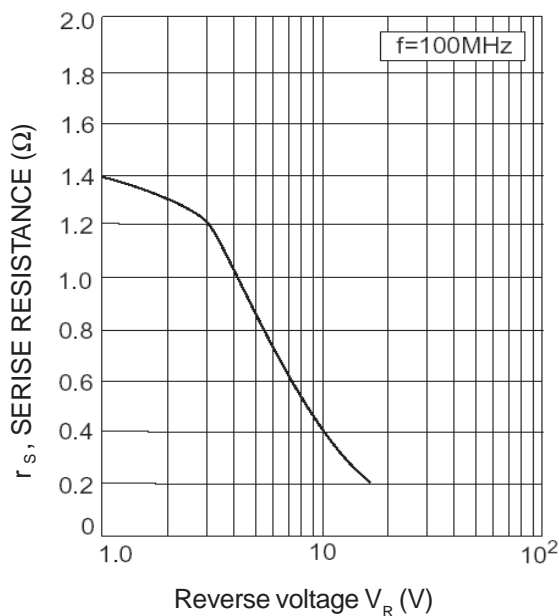


Fig.3 Series resistance Vs. Reverse voltage

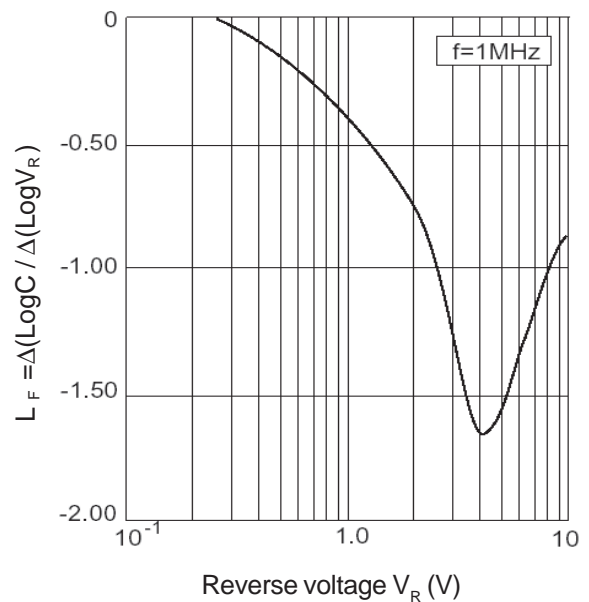


Fig.4 Linearity factor Vs. Reverse voltage